

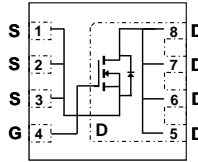
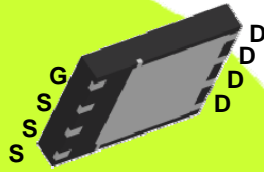
N-Channel CICLON NexFET™ Power MOSFETs CSD16321Q5



Features

- Optimized for 5V gate drive
- Ultra Low Qg & Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant

QFN 5mm x 6mm Plastic Package



Top View

Product Summary

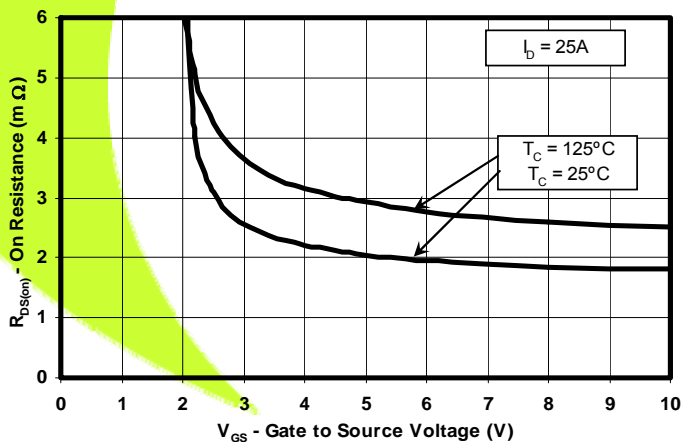
V_{DS}	25	V
Q_g	14	nC
Q_{gd}	2.5	nC
$R_{DS(on)}$	$V_{GS} = 3.0V$	2.8 m Ω
	$V_{GS} = 4.5V$	2.1 m Ω
	$V_{GS} = 8.0V$	1.9 m Ω
V_{th}	1.1	V

Maximum Values ($T_A = 25^\circ C$ unless otherwise stated)

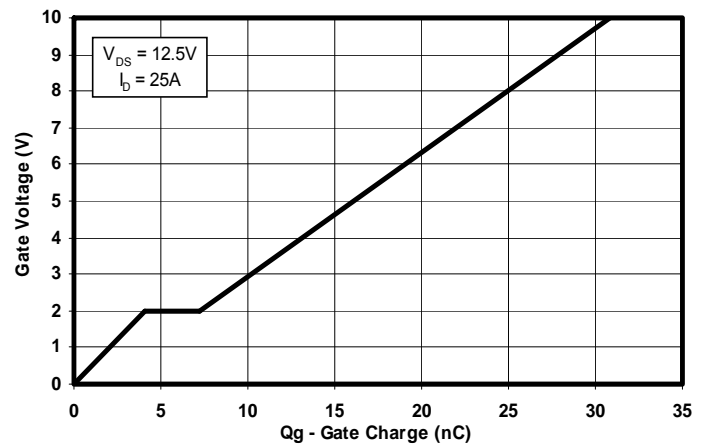
Symbol	Parameter	Value	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -6	V
I_D	Continuous Drain Current, $T_C = 25^\circ C$	100	A
	Continuous Drain Current ¹	31	A
I_{DM}	Pulsed Drain Current, $T_A = 25^\circ C$ ²	200	A
P_D	Power Dissipation ¹	3.1	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	$^\circ C$
E_{AS}	Avalanche Energy, single pulse $I_D = 66A, L = 0.1mH, R_G = 25\Omega$	218	mJ

1. $R_{\theta JA} = 39^\circ C/W$ on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
2. See Figure 10

$R_{DS(on)}$ vs. V_{GS}



Gate Charge



Ordering Information

Type	Package	Package Media	Qty	Ship
CSD16321Q5	QFN 5X6 Plastic Package	13 inch reel	2500	Tape and Reel

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CSD16321Q5



Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25	—	—	V
I_{DSS}	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$	—	—	1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = 10V$	—	—	100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.9	1.1	1.4	V
$R_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 3.0V, I_D = 25A$	—	2.8	3.5	$m\Omega$
		$V_{GS} = 4.5V, I_D = 25A$	—	2.1	2.6	$m\Omega$
		$V_{GS} = 8.0V, I_D = 25A$	—	1.9	2.4	$m\Omega$
g_{fs}	Transconductance	$V_{DS} = 12.5V, I_D = 25A$	—	150	—	S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V$ $f = 1MHz$	—	2360	3100	pF
C_{OSS}	Output Capacitance		—	1700	2200	pF
C_{RSS}	Reverse Transfer Capacitance		—	115	150	pF
R_g	Series Gate Resistance		—	1.2	—	Ω
Q_g	Gate Charge Total (4.5V)	$V_{DS} = 12.5V, I_D = 25A$	—	14	19	nC
Q_{gd}	Gate Charge Gate to Drain		—	2.5	—	nC
Q_{gs}	Gate Charge Gate to Source		—	4.0	—	nC
$Q_{g(th)}$	Gate Charge at V_{th}		—	2.1	—	nC
Q_{OSS}	Output Charge	$V_{DS} = 15V, V_{GS} = 0V$	—	36	—	nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 12.5V$ $V_{GS} = 4.5V, I_D = 25A$ $R_G = 2.7\Omega$	—	11	—	ns
t_r	Rise Time		—	19	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	40	—	ns
t_f	Fall Time		—	30	—	ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	$I_S = 25A, V_{GS} = 0V$	—	0.8	1.0	V
Q_{rr}	Reverse Recovery Charge	$V_{dd} = 13V, I_F = 25A,$ $di/dt = 300A/\mu s$	—	33	—	nC
t_{rr}	Reverse Recovery Time	$V_{dd} = 13V, I_F = 25A,$ $di/dt = 300A/\mu s$	—	32	—	ns

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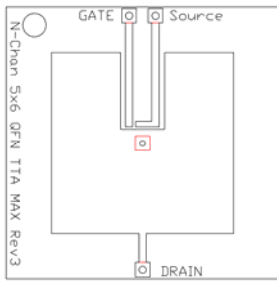
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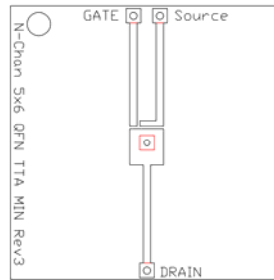
Thermal Characteristics (T_A = 25°C unless otherwise stated)

Symbol	Parameter	Min	Typ	Max	Units
Thermal Characteristics					
R _{θJC}	Thermal Resistance Junction to Case ³	—	—	1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ^{3,4}	—	—	50	°C/W

- R_{θJC} is determined with the device mounted on a 1in square 2 oz. Cu pad on a 1.5x1.5 in .060in thick FR4 board. R_{θJC} is guaranteed by design while R_{θca} is determined by the user's board design.
- Device mounted on FR4 Material with 1in² of 2 oz. Cu.



Max R_{θJA} = 48°C/W when mounted on 1in² of 2 oz. Cu.



Max R_{θJA} = 115°C/W when mounted on min pad area of 2 oz. Cu.

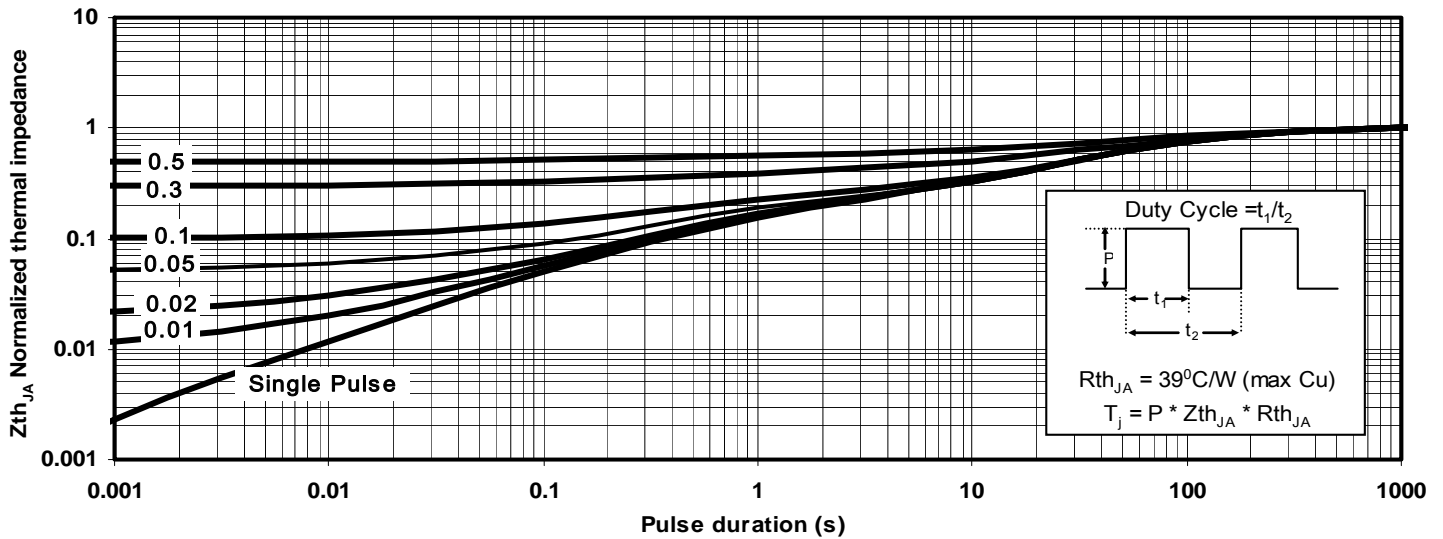


Figure 1: Transient Thermal Impedance

Typical MOSFET Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

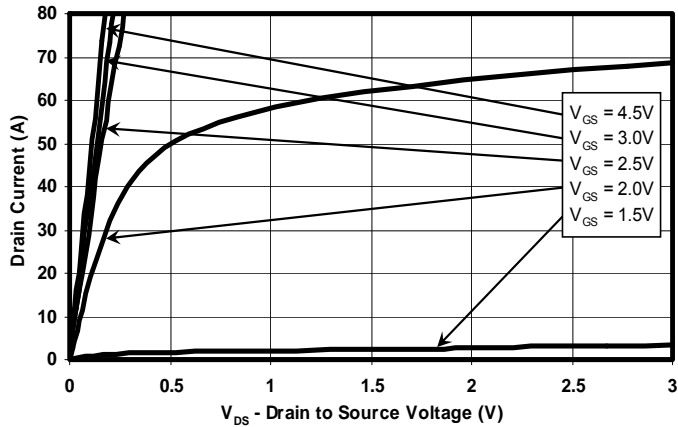


Figure 2: Saturation Characteristics

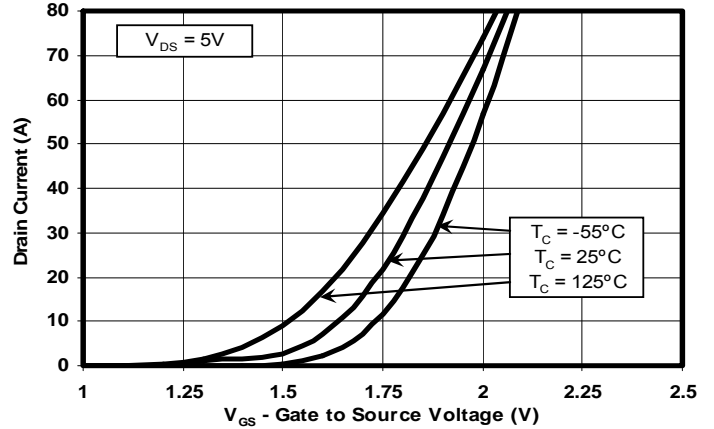


Figure 3: Transfer Characteristics

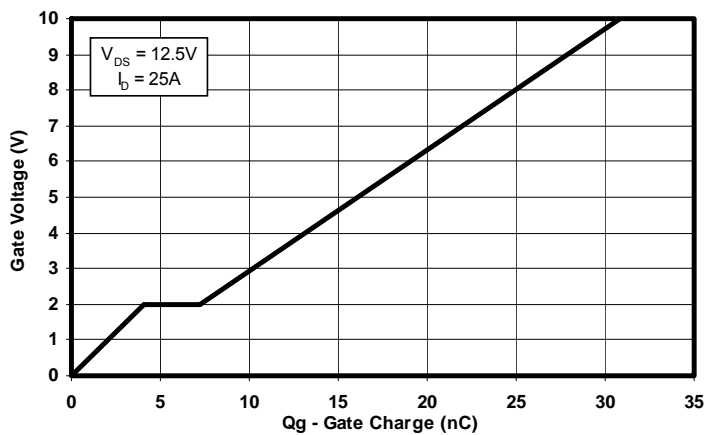


Figure 4: Gate Charge

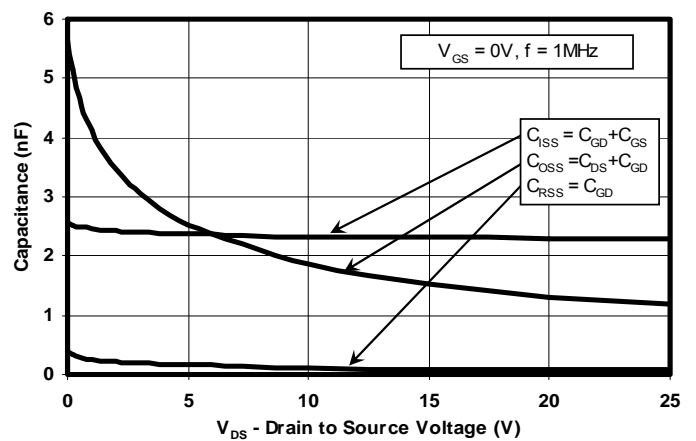


Figure 5: Capacitance

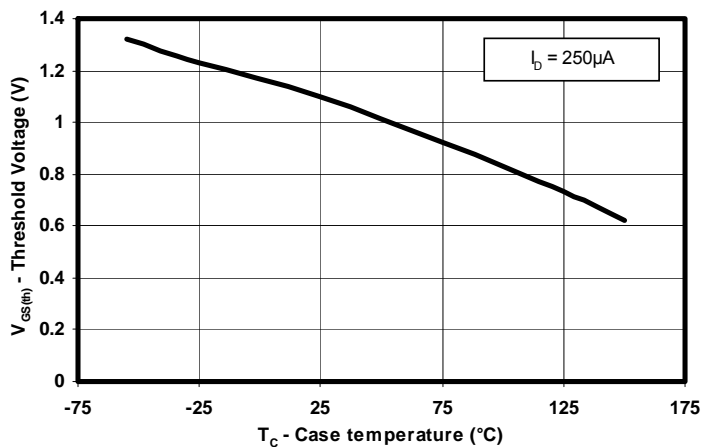


Figure 6: Threshold Voltage vs. Temperature

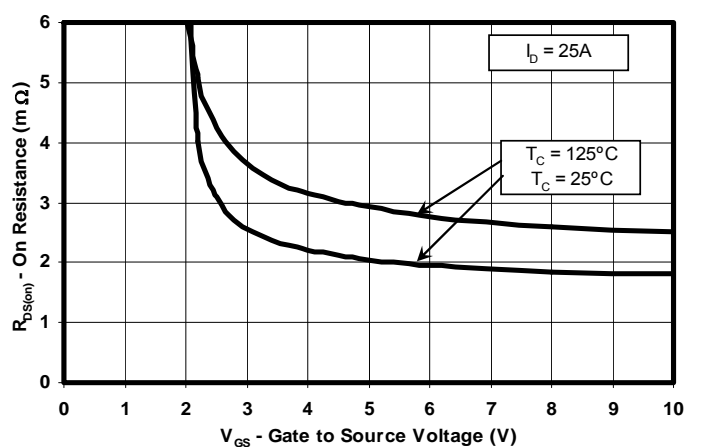


Figure 7: On Resistance vs. Gate Voltage

Typical MOSFET Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise stated)

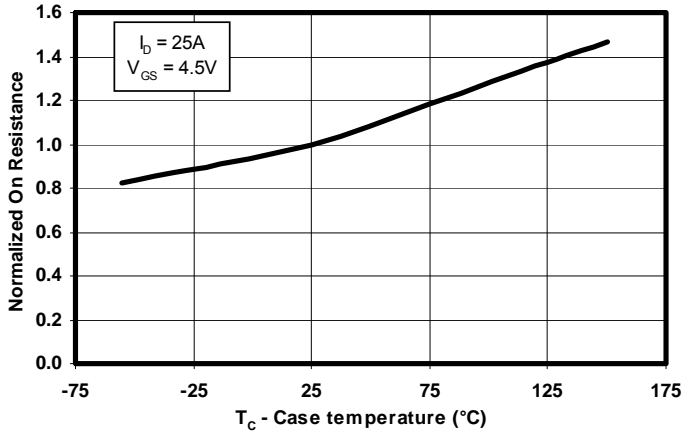


Figure 8: On Resistance vs. Temperature

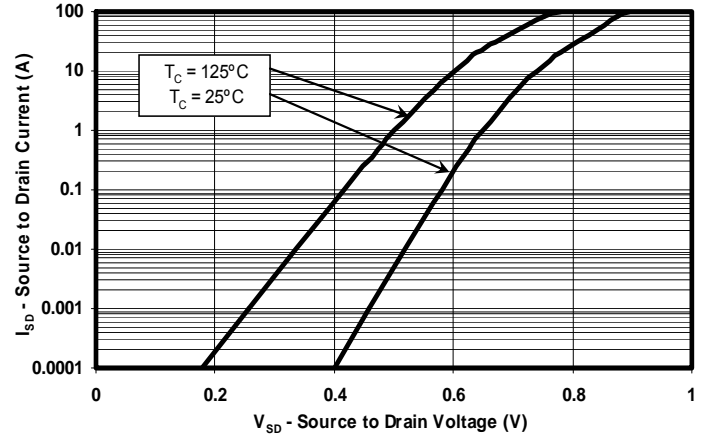


Figure 9: Typical Diode Forward Voltage

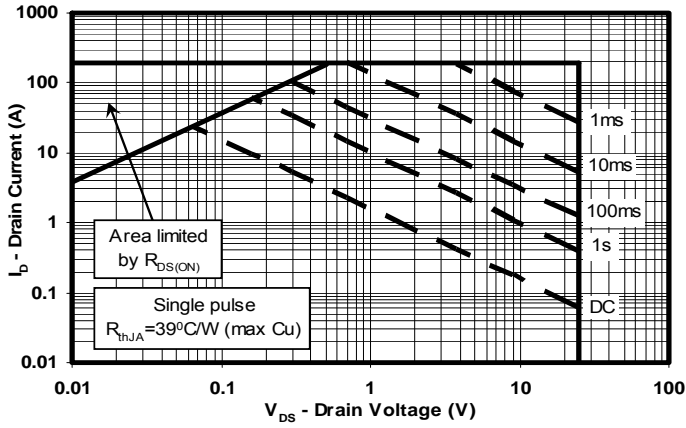


Figure 10: Maximum Safe Operating Area

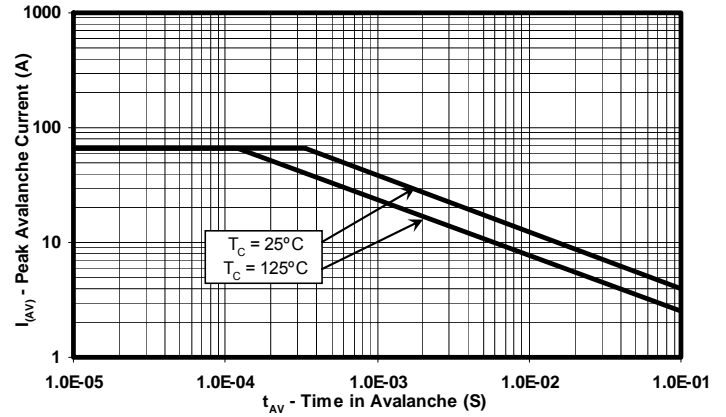


Figure 11: Single Pulse Unclamped Inductive Switching

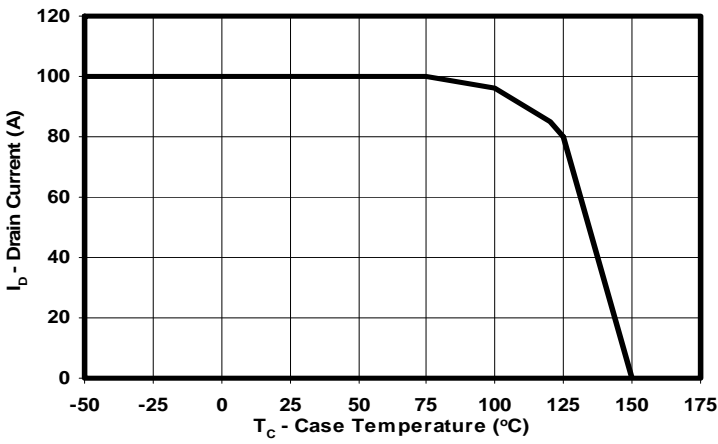


Figure 12: Maximum Drain Current vs. Temperature

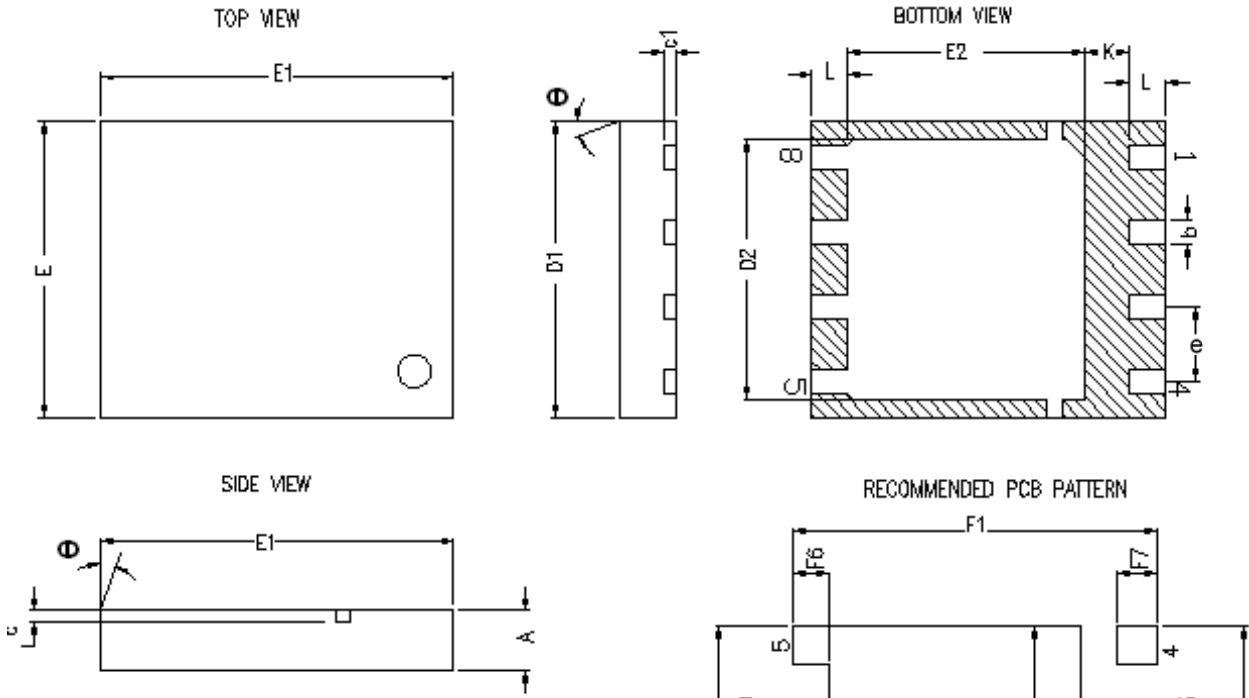
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Q5 Package Dimensions



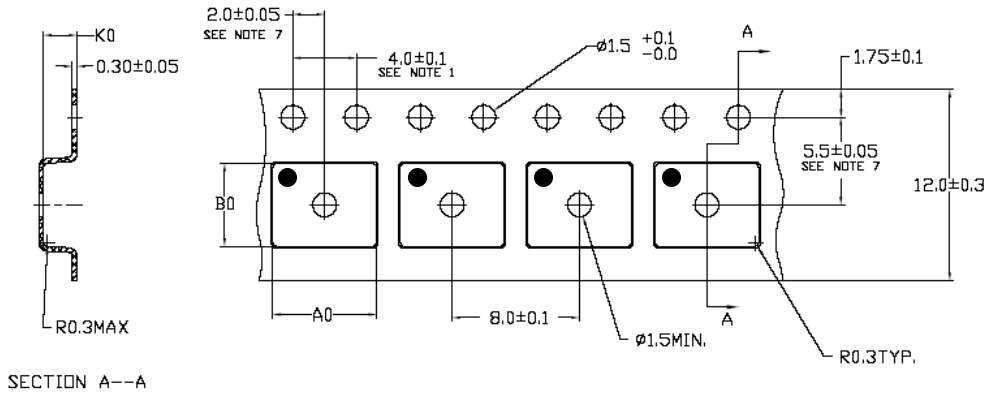
DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
c	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900	5.100	0.193	0.201
D2	4.320	4.520	0.170	0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	4.12	0.154	0.162
e	1.27 TYP		0.050	
L	0.510	0.710	0.020	0.028
θ	0.00	-	-	-
K	0.760	-	0.030	-
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

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Q5 Tape and Reel Information



$A0 = 6.5 \pm 0.1$
 $B0 = 5.3 \pm 0.1$
 $K0 = 1.4 \pm 0.1$

Note:

1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE ± 0.2
2. CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm
3. MATERIAL: BLACK STATIC DISSIPATIVE POLYSTYRENE
4. ALL DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED)
5. THICKNESS: 0.30 ± 0.05 mm

Package Marking Information

Location:

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

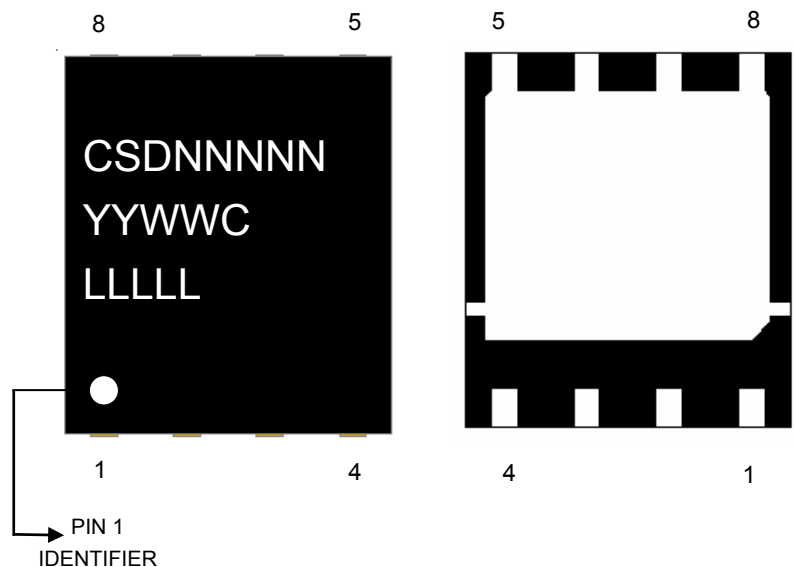
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLLL = Last 5 digits of the Wafer Lot #



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CICLON Semiconductor Device Corp.
116 Research Drive, Bethlehem, PA 18015
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